

SHEET 1 OF 1

INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.  
61352-041SERIAL NO.  
10/620,432APPLICANT  
Hiroyuki FURUYA, et al.FILING DATE  
July 17, 2003GROUP  
2812

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number & - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 2001-176813 A (w/ English Abstract)	06/29/2001	NICHIA CHEM. IND., LTD.			
		JP 2001-342100 A (w/ partial English translation)	12/11/2001	TOSHIBA CORP.			
		EP 1 278 233 A1 (WO 01/084608)	01/22/2003	TOYODA GOSEI CO., LTD.			
		JP 2001-168042 A (w/ English Abstract)(WO 00/55893)	08/22/2001	MITSUBISHI CABLE IND., LTD.			
		EP 1 184 897 A1	03/06/2000	MITSUBISHI CABLE IND., LTD.			
		JP 2001-83837 A (w/ English Abstract)	04/06/2001	CANON INC.			
		J 2002-353152 A (w/ English Abstract)	12/06/2002	MATSUSHITA ELECTRIC IND. CO., LTD.			
		JP 2002-110569 A (w/ English Abstract)	04/12/2002	MATSUSHITA ELECTRIC IND. CO., LTD.			
		JP 2000-228539 A (w/ English Abstract)	08/15/2000	SHARP CORP.			
		JP 11-191657 (w/ English Abstract)	07/13/1999	NICHIA CHEM. IND., LTD.			
		JP 2001-313259 A		Copy not enclosed.			
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		JP 2000-156002 A		Copy not enclosed.			
		JP 2000-331947 A		Copy not enclosed.			
		JP 2000-331937 A		Copy not enclosed.			
		KR 2010583 A		Copy not enclosed.			

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

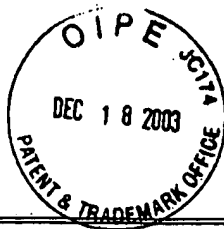
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		I. KIDOGUCHI et al., "Improvement of Crystalline Quality in GaN Films by Air-Bridged Lateral Epitaxial Growth", Jpn. J. Appl. Phys., Part 2, Vol. 39, No. 5B, (2000), pages L453-456.
		S. NAKAMURA, "InGaN/GaN/A1GaN-based laser diodes grown on epitaxially laterally overgrown GaN", Journal of Materials Research, Commentaries and Reviews, Vol. 14, No. 7, July 1999, pages 2716-2731.
		S. NAKAMURA et al., "High-Power, Long-Lifetime InGaN/GaN/A1GaN-Based Laser Diodes Grown on Pure GaN Substrates", Jpn. J. Appl. Phys., Vol. 37, 15 March 1998, pages L309-L312.

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.



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